Ordering number:EN2406

DFB20T

Diffused Junction Type Silicon Diode

2.0A Power Rectifier

Features

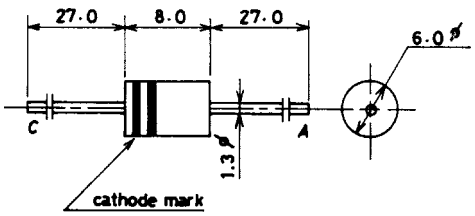
- High-speed switching use.
- Reverse recovery time trr=0.15μs max (B, C, E, G).
  trr=0.3μs max (J, L).
- Peak reverse voltage:V_{RM}=100 to 1000V
- Average Rectified current I_O=2.0A

Package Dimensions

unit:mm

1177

[DFB20T]



C:Cathode
A:Anode

Specifications

Absolute Maximum Ratings at Ta = 25˚C

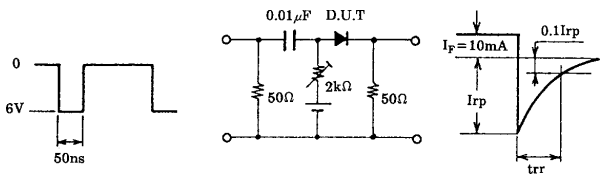
Parameter	Symbol	Conditions	DFB20TB	DFB20TC	DFB20TE	DFB20TG	Unit
Peak Reverse Voltage	V_{RM}		100	200	400	600	V
Average Recitified Current	I_O	Ta=40˚C	→	→	→	2.0	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	→	→	→	120	A
Junction Temperature	Tj		→	→	→	150	˚C
Storage Temperature	Tstg		→	→	→	–40 to +150	˚C

Parameter	Symbol	Conditions	DFB20TJ	DFB20TL			Unit
Peak Reverse Voltage	V_{RM}		800	1000			V
Average Rectified Current	I_O	Ta=40˚C	→	2.0			A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	→	70			A
Junction Temperature	Tj		→	125			˚C
Storage Temperature	Tstg		→	–40 to +150			˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	V_F	I_F=2.0A (B, C, E, G)			1.2	V
		IF=2.0A (J, L)			1.5	V
Reverse Current	I_R	V_R:At each V_{RM}			10	μA
Reverse Recovery Time	trr	I_F=2mA, V_R=15V (B,C, E, G)			0.15	μs
		I_F=2mA, VR=15V (J, L)			0.3	μs

Reverse Recovery Time Test Circuit



Unit (resistance:Ω, capacitance:F)

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